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**2N3970**  
**2N3971**  
**2N3972**

MAXIMUM RATINGS

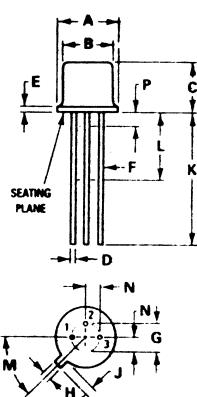
Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	40	Vdc
Drain-Gate Voltage	V <sub>DG</sub>	40	Vdc
Reverse Gate-Source Voltage	V <sub>GSR</sub>	40	Vdc
Forward Gate Current	I <sub>GF</sub>	50	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.8 10	Watts mW°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +200	°C

ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Gate-Source Breakdown Voltage (I <sub>G</sub> = 1.0 μAdc, V <sub>GS</sub> = 0)	V <sub>(BR)GSS</sub>	40	—	Vdc
Gate Reverse Current (V <sub>GS</sub> = 20 Vdc, V <sub>DS</sub> = 0)	I <sub>GSS</sub>	—	250	pAde
Drain Reverse Current (V <sub>DG</sub> = 20 Vdc, I <sub>G</sub> = 0) (V <sub>DG</sub> = 20 Vdc, I <sub>G</sub> = 0, T <sub>A</sub> = 150°C)	I <sub>DGO</sub>	— 500	250 500	pAde nAde
Drain Cutoff Current (V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = -12 Vdc) (V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = -12 Vdc, T <sub>A</sub> = 150°C)	I <sub>D(off)</sub>	— 500	250 500	pAde nAde
Gate Source Voltage (V <sub>DS</sub> = 20 Vdc, I <sub>D</sub> = 1.0 mAde)	V <sub>GS</sub>	4.0 2.0 0.5	10 5.0 3.0	Vdc
<b>ON CHARACTERISTICS</b>				
Zero-Gate-Voltage Drain Current(1) (V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0)	I <sub>DSS</sub>	50 25 5.0	150 75 30	mAde
Drain-Source On-Voltage (I <sub>D</sub> = 20 mAde, V <sub>GS</sub> = 0) (I <sub>D</sub> = 10 mAde, V <sub>GS</sub> = 0) (I <sub>D</sub> = 5.0 mAde, V <sub>GS</sub> = 0)	V <sub>DS(on)</sub>	— — —	1.0 1.5 2.0	Vdc
Static Drain-Source On Resistance (I <sub>D</sub> = 1.0 mAde, V <sub>GS</sub> = 0)	r <sub>DS(on)</sub>	— — —	30 60 100	Ohms
<b>SMALL-SIGNAL CHARACTERISTICS</b>				
Drain-Source "ON" Resistance (V <sub>GS</sub> = 0, I <sub>D</sub> = 0, f = 1.0 kHz)	r <sub>ds(on)</sub>	— — —	30 60 100	Ohms
Input Capacitance (V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>iss</sub>	—	25	pF
Reverse Transfer Capacitance (V <sub>DS</sub> = 0, V <sub>GS</sub> = -12 Vdc, f = 1.0 MHz)	C <sub>rss</sub>	—	6.0	pF
<b>SWITCHING CHARACTERISTICS</b>				
Turn-On Delay Time	Test Condition for 2N3970: (V <sub>DD</sub> = 10 Vdc, V <sub>GS(on)</sub> = 0, I <sub>D(on)</sub> = 20 mAde, V <sub>GS(off)</sub> = 10 Vdc) 2N3970 2N3971 2N3972	t <sub>d(on)</sub>	— — —	10 15 40
Rise Time		t <sub>r</sub>	— — —	10 15 40
Turn-Off Time		t <sub>off</sub>	— — —	30 60 100

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 3.0%.

TO-18 METAL



PIN 1. SOURCE  
2. DRAIN  
3. GATE AND  
CASE

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	5.31	5.84	0.209	0.230
B	4.52	4.95	0.178	0.195
C	4.32	5.33	0.170	0.210
D	0.406	0.533	0.016	0.021
E	—	0.762	—	0.030
F	0.406	0.483	0.016	0.019
G	2.54 BSC	—	0.100 BSC	—
H	0.914	1.17	0.036	0.046
J	0.711	1.22	0.028	0.048
K	1.27	—	0.050	—
L	6.35	—	0.250	—
M	4.5 BSC	—	0.180 BSC	—
N	1.27 BSC	—	0.050 BSC	—
P	—	1.27	—	0.050



Quality Semi-Conductors